

7. (Original) The semiconductor structure of claim 1, wherein said monocrystalline material layer comprises at least one of a semiconductor material, a compound semiconductor material, a metal, an oxide, and a non-metal.

Claims 8-15 (Cancelled)

16. (Original) The semiconductor structure of claim 1, wherein said monocrystalline substrate is characterized by a first lattice constant, said monocrystalline material layer is characterized by a second lattice constant that is different from said first lattice constant, and said binary metal oxide material layer is characterized by a third lattice constant that is different from said first and said second lattice constant.

17. (Original) The semiconductor structure of claim 2, wherein said substrate comprises silicon and said amorphous intermediate layer comprises a silicon oxide.

Claims 18-54 (Cancelled)